

MQ012K1EPX LDMOS TRANSISTOR

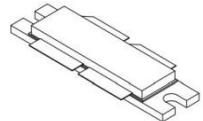
Document Number: MQ012K1EPX
Advanced Datasheet V1.0

2100W, 65V High Power RF LDMOS FETs

Description

The MQ012K1EPX is a 2100W capable, highly rugged, unmatched LDMOS FET, designed for commercial and industrial applications with frequencies HF to 250MHz. It is featured for industry leading high power and high ruggedness, suitable for Industrial, Scientific and Medical application, as well as HF communication, VHF TV and Aerospace applications.

MQ012K1EPX



Freq(MHz)	Voltage(V)	Signal type	Pin(dBm)	Pout(W)	Power Gain(dB)	Eff(%)	Remark
108	65	Pulsed CW	47	2150	16.3	82	Balun
108	50	CW	44	1250	17	82	Balun

Features

- High breakdown voltage 190V to enable possible class E operation at lower Vdd up to 50V
- Qualified up to a maximum of VDS = 65 V Class AB
- Characterized from 36 V to 65 V to support a wide range of applications
- High Efficiency and Linear Gain Operations
- On chip RC network enable high stability and ruggedness
- Integrated ESD Protection
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Excellent thermal stability, low HCl drift
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain—Source Voltage	V _{DSS}	190	Vdc
Gate—Source Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V _{DD}	+65	Vdc
Storage Temperature Range	T _{STG}	-65 to +150	°C
Case Operating Temperature	T _C	+150	°C
Operating Junction Temperature	T _J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case ,Case Temperature 85°C, 1700W CW, 65 Vdc, IDQ = 240 mA	R _{θJC}	TBD	°C/W
Transient thermal impedance from junction to case T _j = 150° C; t _p = 100 us; Duty cycle = 20 %	Z _{th}	TBD	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22—A114)	Class 2

MQ012K1EPX LDMOS TRANSISTOR

Document Number: MQ012K1EPX
Advanced Datasheet V1.0

Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)

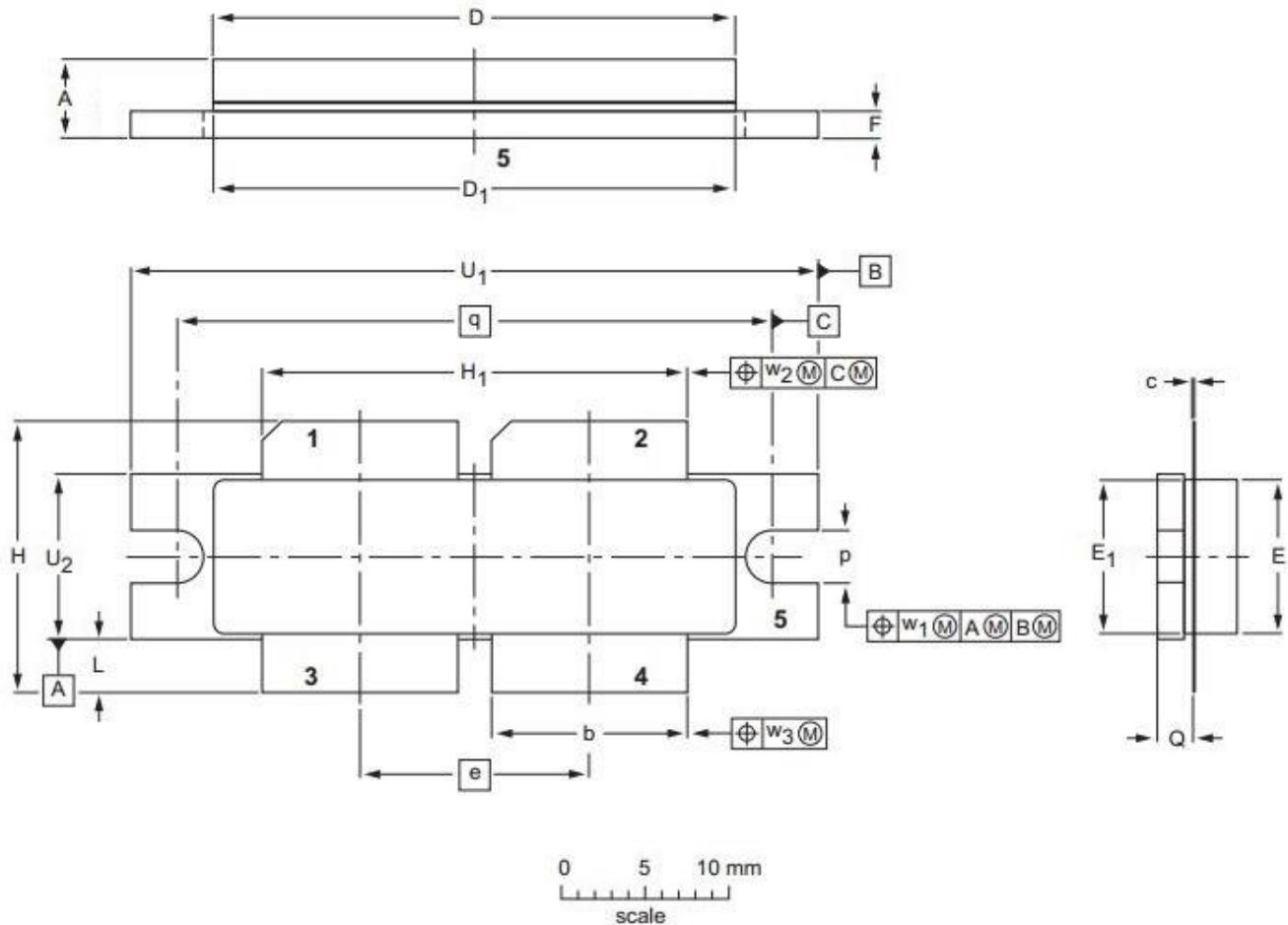
Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics					
Drain-Source Voltage (V _{GS} =0V, I _{DS} =20.0 mA)	V _{(BR)DSS}		190		V
Zero Gate Voltage Drain Leakage Current (V _{DS} = 55V, V _{GS} = 0 V)	I _{DSS}	—	—	1	µA
Gate—Source Leakage Current (V _{GS} = 10 V, V _{DS} = 0 V)	I _{GSS}	—	—	1	µA
Gate Threshold Voltage (V _{DS} = 55V, I _D = 600 µA)	V _{GS(th)}	—	2.6	—	V
Gate Quiescent Voltage (V _{DD} = 60 V, I _D = 240 mA, Measured in Functional Test)	V _{GS(Q)}	—	3	—	V
Drain source on state resistance (V _{DS} = 0.1V, V _{GS} = 10 V) Each section side of device measured	R _{DS(on)}		100		mΩ
Common Source Input Capacitance (V _{GS} = 0V, V _{DS} = 65 V, f = 1 MHz) Each section side of device measured	C _{ISS}		1120		pF
Common Source Output Capacitance (V _{GS} = 0V, V _{DS} = 65 V, f = 1 MHz) Each section side of device measured	C _{OSS}		180		pF
Common Source Feedback Capacitance (V _{GS} = 0V, V _{DS} = 65 V, f = 1 MHz) Each section side of device measured	C _{RSS}		3.9		pF

MQ012K1EPX LDMOS TRANSISTOR

Document Number: MQ012K1EPX
Advanced Datasheet V1.0

Package Outline

Flanged ceramic package; 2 mounting holes; 4 leads (1, 2—DRAIN, 3, 4—GATE, 5—SOURCE)



UNIT	A	b	c	D	D ₁	e	E	E ₁	F	H	H ₁	L	p	Q	q	U ₁	U ₂	W ₁	W ₂	W ₃
mm	4.7	11.81	0.18	31.55	31.52	13.72	9.50	9.53	1.75	17.12	25.53	3.48	3.30	2.26	35.56	41.28	10.29	0.25	0.51	0.25
	4.2	11.56	0.10	30.94	30.96		9.30	9.27	1.50	16.10	25.27	2.97	3.05	2.01		41.02	10.03			
inches	0.185	0.465	0.007	1.242	1.241	0.540	0.374	0.375	0.069	0.674	1.005	0.137	0.130	0.089	1.400	1.625	0.405	0.01	0.02	0.01
	0.165	0.455	0.004	1.218	1.219		0.366	0.365	0.059	0.634	0.995	0.117	0.120	0.079		1.615	0.395			

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-D4E					03/12/2013

MQ012K1EPX LDMOS TRANSISTOR

Document Number: MQ012K1EPX
Advanced Datasheet V1.0

Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2026/1/12	Rev 1.0	Advanced Datasheet

Application data based on SYX-26-02

Disclaimers

Specifications are subject to change without notice. Innogration believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogration for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogration. Innogration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogration in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogration and authorized distributors

Copyright © by Innogration (Suzhou) Co.,Ltd.